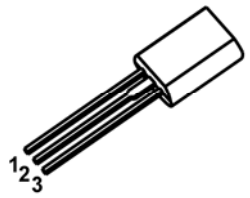
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92MOD Plastic-Encapsulate Transistors

2SB740 TRANSISTOR (PNP)

TO – 92MOD



1. EMITTER
2. COLLECTOR
3. BASE

FEATURES

- Low Frequency Power Amplifier
- Complementary Pair with 2SD789

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-70	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current	-1	A
P_C	Collector Power Dissipation	900	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	139	℃/W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~+150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-10μA,I_E=0	-70			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA,I_B=0	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-10μA,I_C=0	-6			V
Collector cut-off current	I_{CBO}	V_{CB}=-55V,I_E=0			-1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-6V,I_C=0			-0.2	μA
DC current gain	h_{FE}	V_{CE}=-2V, I_C=-100mA	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-1A,I_B=-100mA			-0.6	V
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0, f=1MHz		35		pF
Transition frequency	f_T	V_{CE}=-2V,I_C=-10mA		150		MHz

CLASSIFICATION OF h_{FE}

RANK	B	C
RANGE	100-200	160-320